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Table of Contents

Technical Sessions A1L-A: SiC Devices 1

Nov. 3, 2015 11:15 am – 12:30 pm

Session chair: Avinash Kashyap, John Hostetler

[Short Circuit Robustness of 1200 V SiC Switches](#) 1

Ranbir Singh, *GeneSiC Semiconductor Inc.*
Brian Grummel, *GeneSiC Semiconductor Inc.*
Siddarth Sundaresan, *GeneSiC Semiconductor Inc.*

[Study of the Turn-on of Various High-Voltage SiC Thyristors](#)5

Heather O'Brien, *U.S. Army Research Laboratory*
Aderinto Ogunniyi, *U.S. Army Research Laboratory*
William Shaheen, *Berkeley Research Associates*
Sei-Hyung Ryu, *Wolf Speed*

[Performance Evaluation and Characterization of 6500V Asymmetric SiC NPNP Thyristor based Current Switch](#) 10

Ankan De, *U.S. North Carolina State University*
Subhashish Bhattacharya, *North Carolina State University*
Ranbir Singh, *GeneSiC Semiconductor Inc.*

Technical Sessions A1L-B: GaN Devices 1

Nov. 3, 2015 11:15 am – 12:30 pm

Session chairs: Sameh Khalil, Siddharth Rajan

[Power Switching Transistors Based on GaN and AlGaN Channels](#).....16

Sanyam Bajaj, *The Ohio State University*
Ting-Hsiang Hung, *The Ohio State University*
Fatih Akyol, *The Ohio State University*
Sriram Krishnamoorthy, *The Ohio State University*
Sadia Khandaker, *The Ohio State University*
Andrew Armstrong, *Sandia National Laboratories*
Andrew Allerman, *Sandia National Laboratories*
Siddharth Rajan, *The Ohio State University*

[HV GaN Reliability and Status](#).....21

Sameh G. Khalil, *Infineon Technologies*
Shyam Hardikar, *Infineon Technologies*
Steffen Sack, *Infineon Technologies*
Eric Persson, *Infineon Technologies*
Mohamed Imam, *Infineon Technologies*

Tim McDonald, *Infineon Technologies*

[Study of the Effects of Barrier and Passivation Nitride Stresses on AlGaIn/GaN HEMT Performance using TCAD Simulation](#)24

Hiu Yung Wong, *Synopsys, Inc.*

Nelson Braga, *Synopsys, Inc.*

R. V. Mickevicius, *Synopsys, Inc.*

Jie Liu, *Synopsys, Inc.*

Technical Sessions A1L-C: Gate Drive Circuit 1

Nov. 3, 2015 11:15 am – 12:30 pm

Session chair: *Xin Wu, Zheyu Zhang*

[Realization of High Speed Switching of SiC Power Devices in Voltage Source Converters](#).....28

Zheyu Zhang, *The University of Tennessee, Knoxville*

Fred Wang, *The University of Tennessee, Knoxville*

Leon M. Tolbert, *The University of Tennessee, Knoxville*

Benjamin J. Blalock, *The University of Tennessee, Knoxville*

Daniel J. Costinett, *The University of Tennessee, Knoxville*

[Driving and Sensing Design of an Enhancement-Mode-GaN Phaseleg as a Building Block](#)34

Lingxiao Xue, *Virginia Tech*

Dushan Boroyevich, *Virginia Tech*

Paolo Mattavelli, *DTG-University of Padova, Italy*

[Optimum gate driver design to reach SiC-MOSFET's full potential – speeding up to 200 kV/ \$\mu\$ s](#).....41

Otto Kreuzer, *Fraunhofer IISB*

Bernd Eckardt, *Fraunhofer IISB*

Martin Maerz, *Fraunhofer IISB*

Technical Sessions A2L-A: SiC Devices 2

Nov. 3, 2015 3:30 pm – 5:35 pm

Session chair: *Victor Veliadis, Avinash Kashyap*

[6.9-cm² Active-area Interconnected Wafer 4 kV PiN Diode pulsed at 55 kA](#).....47

V. Veliadis, *Northrop Grumman Electronic Systems*

M. Snook, *Northrop Grumman Electronic Systems*

S. Woodruff, *Northrop Grumman Electronic Systems*

B. Nechay, *Northrop Grumman Electronic Systems*

H. Hearne, *Northrop Grumman Electronic Systems*

C. Lavoie, *Northrop Grumman Electronic Systems*

D. Giorgi, *Omnipulse Inc.*

M. Ingram, *Omnipulse Inc.*

[Excess Carrier Mapping Technique -A New Parameter Extraction Method for 4H-SiC Ambipolar Power Devices](#)51

Meng-Chia Lee, *North Carolina State University*
Xiaoqing Song, *North Carolina State University*
Alex Huang, *North Carolina State University*

[Methodology to Qualify Silicon Carbide MOSFETs for Single Shot Avalanche Events](#).56

V. Pala, *Wolfspeed*
B. Hull, *Wolfspeed*
J. Richmond, *Wolfspeed*
P. Butler, *Wolfspeed*
S. Allen, *Wolfspeed*
J. Palmour, *Wolfspeed*

[SiC MOSFETs Connected in Series with Active Voltage Control](#).....60

Patrick R Palmer, *University of Cambridge*
Jin Zhang, *University of Cambridge*
Xueqiang Zhang, *University of Cambridge*

[Recent Developments in GaN-based Optical Rapid Switching Semiconductor Devices](#).....66

Sudip K. Mazumder, *University of Illinois, Chicago*
Jacob Leach, *Kyma Technologies*
Kevin Udvary, *Kyma Technologies*
Xinmei Wang, *Xi'an University of Technology*

Technical Sessions A2L-B: GaN Devices 2

Nov. 3, 2015 3:30 pm – 5:35 pm

Session chair: Siddharth Rajan, Sameh Khalil

[Floating Body Effects in Carbon Doped GaN HEMTs](#).....70

Martin Kuball, *University of Bristol*
Michael J. Uren, *University of Bristol*
Alexander Pooth, *University of Bristol*
Serge Karboyan, *University of Bristol*
William M. Waller, *University of Bristol*
Indranil Chatterjee, *University of Bristol*

[Reliability and failure physics of GaN HEMT, MISHEMT and p-gate HEMTs for power switching applications](#).....75

Enrico Zanoni, *University of Padova*
Matteo Meneghini, *University of Padova*
Gaudenzio Meneghesso, *University of Padova*
Davide Bisi, *University of Padova*
Isabella Rossetto, *University of Padova*
Antonio Stocco, *University of Padova*

[Activation Energy of Frequency-Dependent Drain-Conductance of AlGaIn/GaN HEMT Evaluated with Low Frequency S-Parameters](#).....81

Akio Wakejima, *Nagoya Institute of Technology*
Tomotaka Narita, *Nagoya Institute of Technology*
Yuki Katayama, *Nagoya Institute of Technology*
Keiichi Tamesue, *Nagoya Institute of Technology*
Takashi Egawa, *Nagoya Institute of Technology*

[Evaluation of 600 V GaN Based Gate Injection Transistors for High Temperature and High Efficiency Applications](#)85

He Li, *The Ohio State University*
Chengcheng Yao, *The Ohio State University*
Chaoran Han, *The Ohio State University*
John Alex Brothers, *The Ohio State University*
Xuan Zhang, *The Ohio State University*
Jin Wang, *The Ohio State University*

[Monolithic Integrated Quasi-Normally-Off Gate Driver and 600 V GaN-on-Si HEMT](#)...92

S. Moench, *University of Stuttgart*
M. Costa, *University of Stuttgart*
A. Barner, *University of Stuttgart*
I. Kalfass, *University of Stuttgart*
R. Reiner, *Fraunhofer Institute for Applied Solid State Physics*
B. Weiss, *Fraunhofer Institute for Applied Solid State Physics*
P. Waltereit, *Fraunhofer Institute for Applied Solid State Physics*
R. Quay, *Fraunhofer Institute for Applied Solid State Physics*
O. Ambacher, *Fraunhofer Institute for Applied Solid State Physics*

Technical Sessions A2L-C: Gate Drive Circuits 2

Nov. 3, 2015 3:30 pm – 5:35 pm

Session chair: *Zheyu Zhang, Xin Wu*

[Cross Conduction Analysis for Enhancement-Mode 650-V GaN HFETs in a Phase-Leg Topology](#).....98

Edward A. Jones, *University of Tennessee*
Fred Wang, *University of Tennessee*
Daniel Costinett, *University of Tennessee*
Zheyu Zhang, *University of Tennessee*
Ben Guo, *United Technologies Research Center*

[Design of a High-Bandwidth Rogowski Current Sensor for Gate-Drive Shortcircuit Protection of 1.7 kV SiC MOSFET Power Modules](#) 104

Jun Wang, *Virginia Polytechnic Institute and State University*
Zhiyu Shen, *Virginia Polytechnic Institute and State University*
Rolando Burgos, *Virginia Polytechnic Institute and State University*
Dushan Boroyevich, *Virginia Polytechnic Institute and State University*

[Gate Drive Development and Empirical Analysis of 10 kV SiC MOSFET Modules](#) ... 108

Andrew N. Lemmon, *The University of Alabama*
Ryan Graves, *The University of Alabama*

[Evaluation and Applications of 600V/650V Enhancement-Mode GaN Devices](#) 113

Xiucheng Huang, *Virginia Tech*

Tao Liu, *Virginia Tech*

Bin Li, *Virginia Tech*

Fred C. Lee, *Virginia Tech*

Qiang Li, *Virginia Tech*

[Ultra-Low Inductance Phase Leg Design for GaN-Based Three-Phase Motor Drive Systems](#) 119

Xuning Zhang, *Virginia Polytechnic Institute and State University*

Nidhi Haryani, *Virginia Polytechnic Institute and State University*

Zhiyu Shen, *Virginia Polytechnic Institute and State University*

Rolando Burgos, *Virginia Polytechnic Institute and State University*

Dushan Boroyevich, *Virginia Polytechnic Institute and State University*

Poster Sessions: Devices

Nov. 3, 2015 5:35 pm – 6:30 pm

Session chair: *Sonny Xue, Robert Kaplar*

[An Extraction Method of Charge Trapping Site Distribution in AlGa_N Layer in GaN HEMT](#)..... 125

T. Baba, *Tokyo Institute of Technology*

K. Kakushima, *Tokyo Institute of Technology*

H. Wakabayashi, *Tokyo Institute of Technology*

K. Tsutsui, *Tokyo Institute of Technology*

H. Iwai, *Tokyo Institute of Technology*

[2-phase 2-stage Capacitor-less Gate Driver for Gallium Nitride Gate Injection Transistor for Reduced Gate Ringing](#)..... 129

Aaron Cai, *Nanyang Technological University*

Arnel C Herrera, *Panasonic Industrial Devices Semiconductor Asia*

Sin Ban How, *Panasonic Industrial Devices Semiconductor Asia*

Liter Siek, *Nanyang Technological University*

[Experimental Performance Comparison of Six-Pack SiC MOSFET and Si IGBT Modules Paralleled in a Half-Bridge Configuration for High Temperature Applications](#)..... 135

S.Tiwari, *Norwegian University of Science and Technology*

O.-M. Midtgard, *Norwegian University of Science and Technology*

T. M. Undeland, *Norwegian University of Science and Technology*

R. Lund, *SmartMotor AS*

[A Novel Charge Based SPICE Model for Nonlinear Device Capacitances](#) 141

Thomas Heckel, *University Erlangen-Nuremberg*

Lothar Frey, *Fraunhofer Institute for Integrated Systems and Device Technology*

[A New AlGa_N/Ga_N Power HFET Employing Partial Deep Trench Drain Structure for High Voltage Application](#) 147

In-Hwan Ji, *North Carolina State University*

Bongmook Lee, *North Carolina State University*
Sizhen Wang, *North Carolina State University*
Veena Misra, *North Carolina State University*
Alex Q. Huang, *North Carolina State University*

[*Comparative Evaluation of 6kV Si and SiC Power Devices for Medium Voltage Power Electronics Applications*](#) 150

Xiaoqing Song, *North Carolina State University*
Alex Q. Huang, *North Carolina State University*
Xijun Ni, *Nanjing Institute of Technology*
Liqi Zhang, *Nanjing Institute of Technology*

[*Thermal characterization of high voltage GaN-on-Si Schottky Barrier Diodes \(SBD\) for designing an on-chip thermal shutdown circuit for a power HEMT*](#)..... 156

D. M. Risbud, *University of California, Santa Cruz*
K. Pedrotti, *University of California, Santa Cruz*
M. Power, *University of Bristol*
J. W. Pomeroy, *University of Bristol*
M. Kuball, *University of Bristol*

[*Suitability of N-ON recessed implanted gate vertical-channel SiC JFETs for optically triggered 1200 V solid-state-circuit-breakers*](#)..... 162

V. Veliadis, *Northrop Grumman Electronic Systems*
B. Steiner, *Texas Tech University*
K. Lawson, *Texas Tech University*
S. B. Bayne, *Texas Tech University*
D. Urciuoli, *U.S. Army Research Laboratory*
H. C. Ha, *Northrop Grumman Electronic Systems*

[*Influences of DBC Metal Layout on the Reliability of IGBT Power Modules*](#) 166

Tian Tian, *Huazhong University of Sci& Tech*
Lin Liang, *Huazhong University of Sci& Tech*
Wei Xin, *Huazhong University of Sci& Tech*
Fang Luo, *Ohio State University*

[*Key Structure and Process for Pulsed Power Switch SiC RSD*](#) 170

Lin Liang, *Huazhong University of Sci & Tech*
Ming Pan, *Huazhong University of Sci & Tech*
Ludan Zhang, *Huazhong University of Sci & Tech*
Yuxiong Shu, *Huazhong University of Sci & Tech*

[*A Discussion on the DC and Switching Performance of a Gallium Nitride CAVET for 1.2kV Application*](#) 174

Dong Ji, *Arizona State University*
Srabanti Chowdhury, *Arizona State University*

[*Comparison of Energy Losses in High-Current 1700 V Switches*](#)..... 180

Siddarth Sundaresan, *GeneSiC Semiconductor Inc.*
Brian Grummel, *GeneSiC Semiconductor Inc.*
Ranbir Singh, *GeneSiC Semiconductor Inc.*

[Performance Evaluation of Series Connected 1700V SiC MOSFET Devices](#).....184
Kasunaidu Vechalapu, *North Carolina State University*
Subhashish Bhattacharya, *North Carolina State University*
Eddy Aleoiza, *ABB Corporate Research Center*

[Turn-on Capability of 22 kV SiC Emitter Turn-off \(ETO\) Thyristor](#).....192
Lin Liang, *North Carolina State University*
Alex Q. Huang, *North Carolina State University*
Woongje Sung, *North Carolina State University*
Meng-Chia Lee, *North Carolina State University*
Xiaoqing Song, *North Carolina State University*
Chang Peng, *North Carolina State University*
Lin Cheng, *Texas Tech University*
John Palmour, *Cree, Inc.*
Charles Scozzie, *U. S. Army Research Laboratory*

Poster Sessions: Applications

Nov. 3, 2015 5:35 pm – 6:30 pm

Session chair: Sonny Xue, Robert Kaplar

[Consideration of Flyback Converter Using GaN Devices](#).....196
Liming Liu, *ABB Inc.*
Joonas Puukko, *ABB Inc.*
Jing Xu, *ABB Inc.*

[Loss Analysis of GaN Devices in an Isolated Bidirectional DC-DC Converter](#).....201
Fei Xue, *North Carolina State University*
Ruiyang Yu, *North Carolina State University*
Suxuan Guo, *Wensong, North Carolina State University*
Wensong Yu, *North Carolina State University*
Alex Q. Huang, *North Carolina State University*

[Two Year Reliability Validation of GaN Power Semiconductors in Low Voltage Power Electronics Applications](#)206
Benjamin K. Rhea, *Auburn University*
Luke L. Jenkins, *Auburn University*
Frank T. Werner, *Auburn University*
William E. Abell, *Auburn University*
Robert N. Dean, *Auburn University*

[Design of a High-Density, Diode-Less 1.2 kV, 90 A SiC MOSFET Half-Bridge Power Module](#)210
Christina DiMarino, *Virginia Tech*
Wenli Zhang, *Virginia Tech*
Rolando Burgos, *Virginia Tech*
Dushan Boroyevich, *Virginia Tech*

[An Optimized Gate-loop Layout for Multi-chip SiC MOSFET Power Modules](#)215
Miao Wang, *The Ohio State University*

Fang Luo, *The Ohio State University*
Longya Xu, *The Ohio State University*

[Efficiency Optimization for a Power Factor Correction \(PFC\) Rectifier with Gallium Nitride Transistor](#)220

Sven Bolte, *University of Paderborn*
Norbert Fröhleke, *University of Paderborn*
Joachim Böcker, *University of Paderborn*

[Integrated SiC MOSFET Module With Ultra Low Parasitic Inductance for Noise Free Ultra High Speed Switching](#)224

Liqi Zhang, *NC State University*
Suxuan Guo, *NC State University*
Xuan Li, *NC State University*
Yang Lei, *NC State University*
Wensong Yu, *NC State University*
Alex Q. Huang, *NC State University*

[Development of Software to Design Passive Filters for EMI Suppression in SiC DC Fed Motor Drives](#)230

Balaji Narayanasamy, *The Ohio State University*
Hussam Jalanbo, *The Ohio State University*
Fang Luo, *The Ohio State University*

[A High Temperature Comparator in CMOS SiC](#)236

A. Rahman, *University of Arkansas*
K. Addington, *University of Arkansas*
M. Barlow, *University of Arkansas*
S. Ahmed, *University of Arkansas*
H. A. Mantooth, *University of Arkansas*
A. M. Francis, *Ozark IC Inc.*

[A SiC 8 Bit DAC at 400°C](#)241

A. Rahman, *University of Arkansas*
S. Roy, *University of Arkansas*
R. C. Murphree, *University of Arkansas*
H. A. Mantooth, *University of Arkansas*
A. M. Francis, *Ozark IC Inc.*
J. Holmes, *Ozark IC Inc.*

[CM Noise Reduction of Isolated Converter by Balancing Technique \(not presented\)](#)

A. Nasir, *Bournemouth University*
Jon Cobb, *Bournemouth University*

[Design Considerations for High Power Density/Efficient PCB Embedded Inductor](#)...247

Mehrdad Biglarbegan, *University of North Carolina at Charlotte*
Neel Shah, *University of North Carolina at Charlotte*
Iman Mazhari, *University of North Carolina at Charlotte*
Babak Parkhideh, *University of North Carolina at Charlotte*

Technical Sessions B1L-A: SiC Devices 3

Nov. 4, 2015 10:45 am – 12:25 pm

Session chair: *John Hostetler, Victor Veliadis*

[*Bias-Temperature Instability in SiC MOSFETs \(presentation only\)*](#)

Aivars Lelis, U. S. Army Research Laboratory

Ron Green, U. S. Army Research Laboratory

Daniel Habersat, U. S. Army Research Laboratory

[*Channel Mobility and Threshold Voltage Characterization of 4H-SiC MOSFET with Antimony Channel Implantation*](#)253

Yongju Zheng, Auburn University

T. Isaacs-Smith, Auburn University

A. C. Ahyi, Auburn University

S. Dhar, Auburn University

P. M. Mooney, Simon Fraser University

[*Understanding Switching Losses in SiC MOSFET: Toward Lossless Switching*](#).....257

Xuan Li, NC State University

Liqi Zhang, NC State University

Suxuan Guo, NC State University

Yang Lei, NC State University

Alex Q. Huang, NC State University

Bo Zhang, University of Electronic Science and Technology of China

[*Characterization and Prediction of the Avalanche Performance of 1.2 kV SiC MOSFETs*](#)263

Christina DiMarino, Virginia Tech

Brett Hull, Wolfspeed

Technical Sessions B1L-B: PFC and Other Applications

Nov. 4, 2015 10:45 am – 12:25 pm

Session chair: *Mark Scott, Fritz Kub*

[*Semiconductor-based Galvanic Isolation*](#).....268

Xuan Zhang, The Ohio State University

He Li, The Ohio State University

Chengcheng Yao, The Ohio State University

Jin Wang, The Ohio State University

[*Design of GaN Transistor-Based Class E DC-DC Converter with Resonant Rectifier Circuit*](#)275

Kyung-Hwan Lee, Seoul National University

Euihoon Chung, Seoul National University

Gab-Su Seo, Seoul National University

Jung-Ik Ha, Seoul National University

[*Operation Analysis of Digital Control based MHz Totem-pole PFC with GaN Device*](#)281

Zhengyang Liu, *Virginia Polytechnic Institute and State University*
Zhengrong Huang, *Virginia Polytechnic Institute and State University*
Fred C. Lee, *Virginia Polytechnic Institute and State University*
Qiang Li, *Virginia Polytechnic Institute and State University*
Yuchen Yang, *Virginia Polytechnic Institute and State University*

[Testing of a Novel Medium Voltage Impedance Measurement Unit](#)287

Karl Schoder, *Florida State University*
Mischa Steurer, *Florida State University*
Ferenc Bogdan, *Florida State University*
John Hauer, *Florida State University*
James Langston, *Florida State University*
Dushan Boroyevich, *Virginia Tech*
Rolando Burgos, *Virginia Tech*
Igor Cvetkovic, *Virginia Tech*
Zhiyu Shen, *Virginia Tech*
Christina DiMarino, *Virginia Tech*

Technical Sessions B1L-C: Power Modules and

Packaging 1

Nov. 4, 2015 10:45 am – 12:25 pm

Session chair: *Shirley Zhang, Timothy Han*

[Assessment of PSpice Model for Commercial SiC MOSFET Power Modules](#)291

Daniel Johannesson, *ABB Corporate Research*
Muhammad Nawaz, *ABB Corporate Research*

[Design of a Silicon-WBG Hybrid Switch](#)296

Amol Deshpande, *The Ohio State University*
Fang Luo, *The Ohio State University*

[6.5kV Enhancement Mode SiC JFET Based Power Module](#).....300

John. L. Hostetler, *United Silicon Carbide, Inc.*
Xueqing Li, *United Silicon Carbide, Inc.*
Peter Alexandrov, *United Silicon Carbide, Inc.*
Xing Huang, *United Silicon Carbide, Inc.*
Anup Bhalla, *United Silicon Carbide, Inc.*
Martin Becker, *Princeton Power Systems*
Joseph Colombo, *Princeton Power Systems*
Derrick Dieso, *Princeton Power Systems*
Jerry Sherbondy, *Powerex*

[Package Influence on the Simulated Performance of 1.2 kV SiC Modules](#).....306

Zichen Miao, *Virginia Tech*
Yincan Mao, *Virginia Tech*
Khai Ngo, *Virginia Tech*
Woochan Kim, *Texas Instrument*

Technical Sessions B2L-A: Renewable and Energy

Storage Applications

Nov. 4, 2015 3:30 pm – 5:35 pm

Session chair: *Fritz Kub, Luis Arnedo*

[DC Ripple Current Reduction on Multilevel, Multiport, Single- Phase DC/AC Converter for Renewable Energy Applications](#)312

Mohammed Alsolami, *The Ohio State University*

Jin Wang, *The Ohio State University*

Luis Herrera, *University of Dayton Research Institute*

[A High Efficiency Inverter Design for Google Little Box Challenge](#).....319

Lanhua Zhang, *Virginia Polytechnic Institute and State University*

Rachael Born, *Virginia Polytechnic Institute and State University*

Xiaonan Zhao, *Virginia Polytechnic Institute and State University*

Jih-Sheng Lai, *Virginia Polytechnic Institute and State University*

[High Power Density Single Phase Inverter Using GaN FETS and Active Power Decoupling for Google Little Box Challenge](#)323

Ahmed S. Morsy, *Texas A&M University*

Michael Bayern, *Texas A&M University*

Prasad Enjeti, *Texas A&M University*

[Sizing SiC Storage Inverters for Fast Grid Frequency Support](#).....328

Anderson Hoke, *National Renewable Energy Laboratory*

Kevin Bennion, *National Renewable Energy Laboratory*

Vahan Gevorgian, *National Renewable Energy Laboratory*

Sudipta Chakraborty, *National Renewable Energy Laboratory*

Eduard Muljadi, *National Renewable Energy Laboratory*

[An E-mode GaN HEMTs Based Three-Level Bidirectional DC/DC Converter Used in Robert Bosch DC-Grid System](#)334

Juncheng Lu, *Kettering University*

Hua (Kevin) Bai, *Kettering University*

Scott Averitt, *Robert Bosch LLC*

Di Chen, *GaN Systems Inc.*

Julian Styles, *GaN Systems Inc.*

Technical Sessions B2L-B: Transportation Applications

Nov. 4, 2015 3:30 pm – 5:35 pm

Session chair: *Luis Arnedo, Mark Scott*

[Advances in SiC-Based Power Conversion for Shipboard Electrical Power Systems](#).341

Terry Ericson, *Ericson Innovations*

Ravisekhar Raju, *GE Global Research*

Rolando Burgos, *Virginia Tech*
Dushan Boroyevich, *Virginia Tech*
Sharon Beermann-Curtin, *U.S. Department of Defense*

[Performance and Cost Considerations for SiC-based HEV Traction Inverter Systems](#).....347

Ming Su, *Ford Motor Company*
Chingchi Chen, *Ford Motor Company*
Shrivatsal Sharma, *Ford Motor Company*
Jun Kikuchi, *Ford Motor Company*

[An Indirect Matrix Converter based 97%-efficiency On-board Level 2 Battery Charger Using E-mode GaN HEMTs](#)351

Juncheng Lu, *Kettering University*
Qi Tian, *Kettering University*
Kevin Bai, *Kettering University*
Alan Brown, *Hella Corporate Center USA Inc.*
Matt McAmmond, *Hella Corporate Center USA Inc.*

[Using SiC MOSFETs to Improve Reliability of EV Inverters](#).....359

Hao Zheng, *South China University of Technology*
Xubin Wang, *South China University of Technology*
Xuemei Wang, *South China University of Technology*
Li Ran, *University of Warwick*
Bo Zhang, *South China University of Technology*

[A 1 MHz eGaN FET Based 4-Switch Buck-Boost Converter for Automotive Applications](#).....365

Chenhao Nan, *Arizona State University*
Tong Yao, *Arizona State University*
Raja Ayyanar, *Arizona State University*

Technical Sessions B2L-C: Power Modules and

Packaging 2

Nov. 4, 2015 3:30 pm – 5:35 pm

Session chair: *David Reusch, Timothy Han*

[High Frequency eGaN Monolithic Half Bridge IC Based 12 VIN to 1 VOUT Point of Load Converter](#)371

David Reusch, *Efficient Power Conversion Corporation*

[Application and Reliability Analysis of Sintered Silver Preforms for Die Attachment of Wide Bandgap Devices](#).....377

Sayan Seal, *University of Arkansas*
Michael D. Glover, *University of Arkansas*
H. Alan Mantooh, *University of Arkansas*

[Reliability and failure analysis of Cu-Sn transient liquid phase sintered \(TLPS\) joints](#)

[under power cycling loads](#)383
S.Ali Moeini, *University of Maryland*
Hannes Greve, *University of Maryland*
F. Patrick McCluskey, *University of Maryland*

[3.38 Mhz Operation of 1.2kV SiC MOSFET With Integrated Ultra-Fast Gate Drive](#).....390
Suxuan Guo, *North Carolina State University*
Liqi Zhang, *North Carolina State University*
Yang Lei, *North Carolina State University*
Xuan Li, *North Carolina State University*
Fei Xue, *North Carolina State University*
Wensong Yu, *North Carolina State University*
Alex Q. Huang, *North Carolina State University*

[Simulation of A Power Package with Underfill Resin and Silicon Gel](#)396
Hao Zhang, *United Silicon Carbide Inc.*
Simon S. Ang, *University of Arkansas*

Plenary Session Paper:

[Wide Bandgap Semiconductor Power Devices for Energy Efficient Systems](#).....402
T. Paul Chow, *Rensselaer Polytechnic Institute*

[Switching and Robustness analysis of 10 kV SiC BJTs](#).....406
Ranbir Singh, *GeneSiC Semiconductor, Inc.*
Stoyan Jeliazkov, *GeneSiC Semiconductor, Inc.*
Brian Grummel, *GeneSiC Semiconductor, Inc.*
Siddarth Sundaresan, *GeneSiC Semiconductor, Inc.*